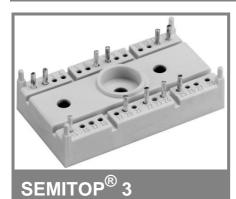
SK 80 D 12 F



Bridge Rectifier

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Preliminary Data

Features

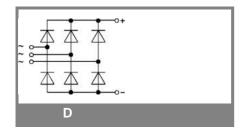
- · Compact design
- · One screw mounting
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DCB
- Fast and soft recovery CAL (Controlled Axial Lifetime) diode
- UL recognized, file no. E 63 532

Typical Applications

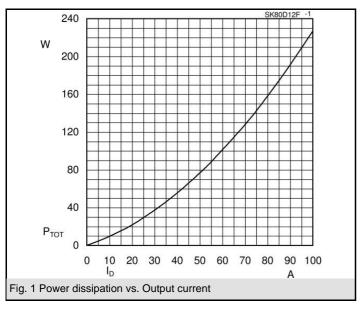
- General power switching applications
- UPS
- SMPS

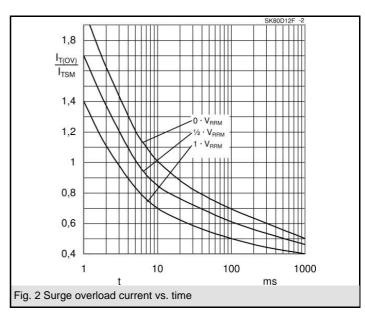
V _{RSM}	V_{RRM}, V_{DRM}	I _D = 80 A (full conduction)
V	V	(T _s = 80 °C)
	1200	SK 80 D 12 F

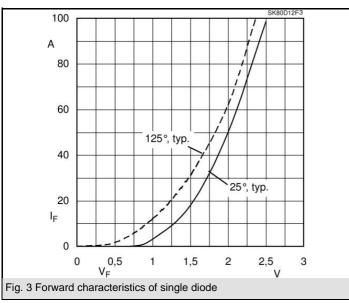
Symbol	Conditions	Values	Units
I _D	T _s = 80 °C	80	А
I _{RRM}	T _{vj} = 125°C (See Fig. 6)	typ. 40	Α
Q_{rr}	T _{vj} = 25 (125)°C (See Fig. 6)	typ. 1,5 (2,7)	μC
I_R	T _{vj} = 25 (150)°C; V _R =V _{RRM}	0,2 (4)	mA
I _{FSM}	T _{vj} = 150 °C; 10 ms	550	A
	$T_{vj} = {^{\circ}C}; ms$		Α
i²t	T _{vj} = 150 °C; 10 ms	1500	A²s
	T _{vj} = °C; ms		A²s
V _F	T _{vi} = 25 °C; I _F = 75 A	max. 2,5	V
$V_{(TO)}$	T _{vi} = 125 °C	max. 1,2	V
r _T	T _{vj} = 125 °C	max. 22	mΩ
I_{RD}	$T_{vj} = {^{\circ}C}; V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$		mA
			mA
R _{th(j-s)}	per diode	0,9	K/W
	per module	0,15	K/W
T _{solder}	terminals, 10s	260	°C
T _{vi}		-40+150	°C
T _{stg}		-40+125	°C
V _{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 (2500)	V
M _s	mounting torque to heatsink	2,5	Nm
Mt			
m	approx. weight	30	g
Case	SEMITOP® 3	T 25	

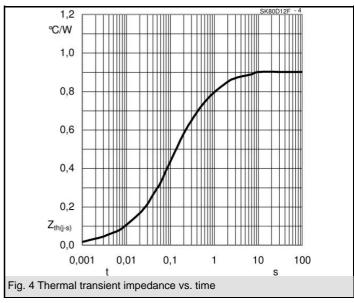


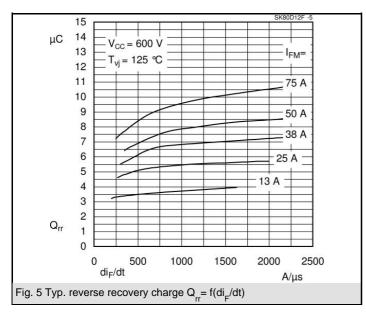
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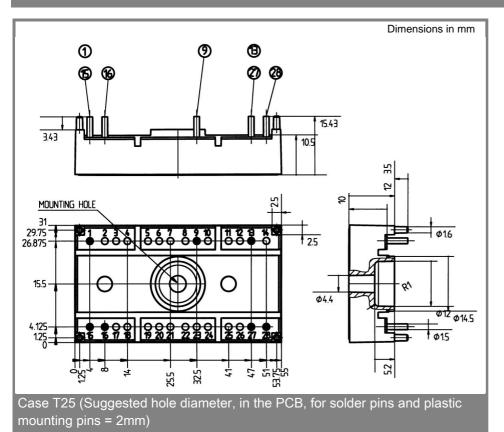


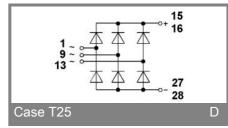
Measurement conditions for switching parameters:

I_F= 50A V_R= 600V

-di/dt = 800A/μs

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